

Fig. 1A (prior Art)

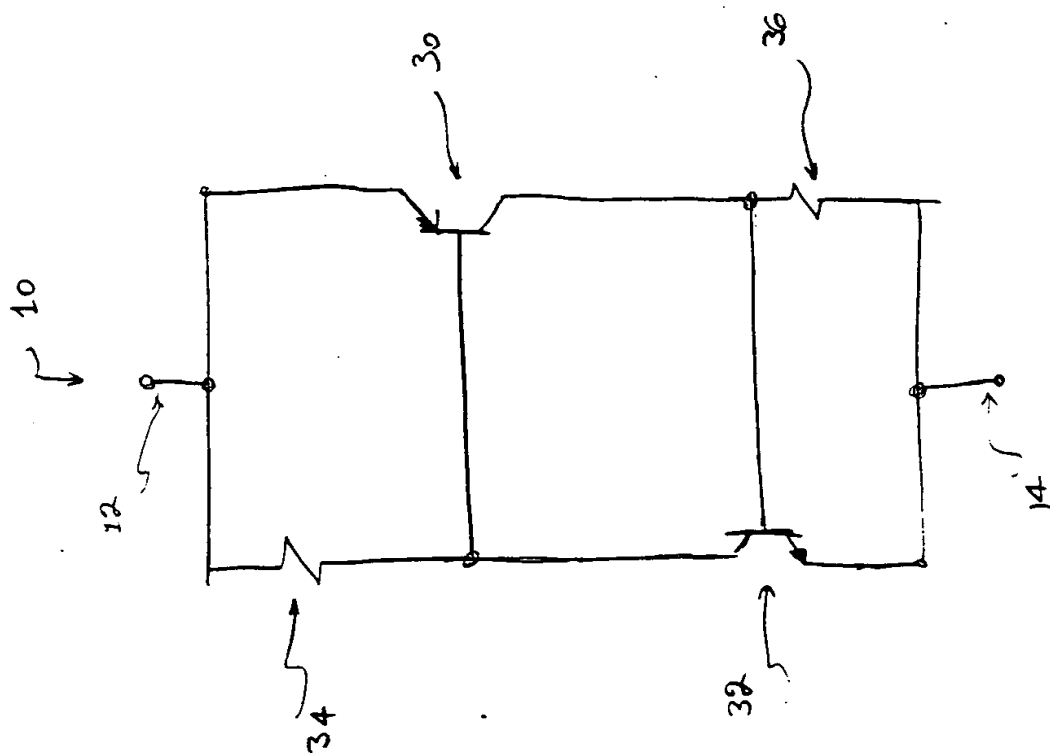


Fig. 1B (prior Art)

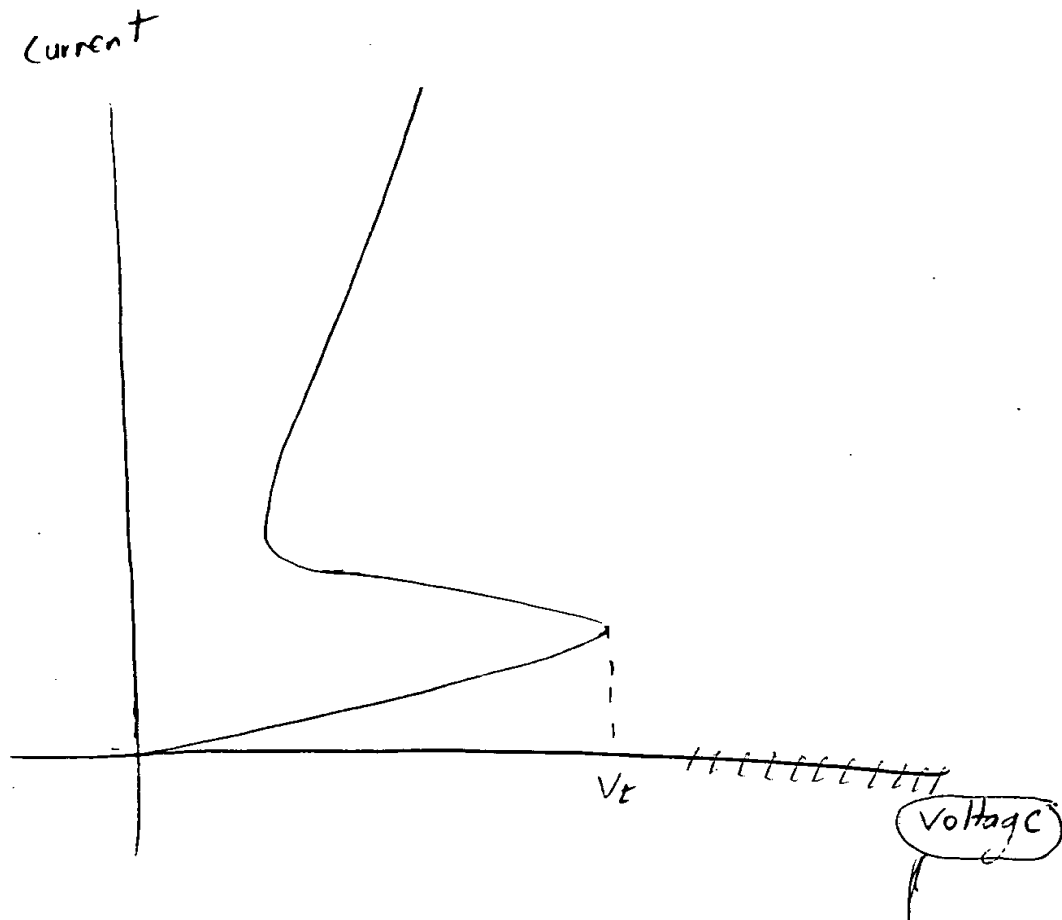
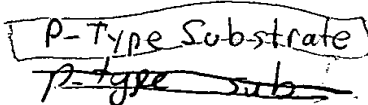
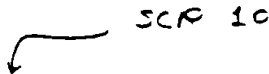


Fig. 1C (prior Art)

Move  
upward  
as to  
begin at  
shortened  
right end of  
horizontal  
axis



24

Fig. 1D (prior Art)

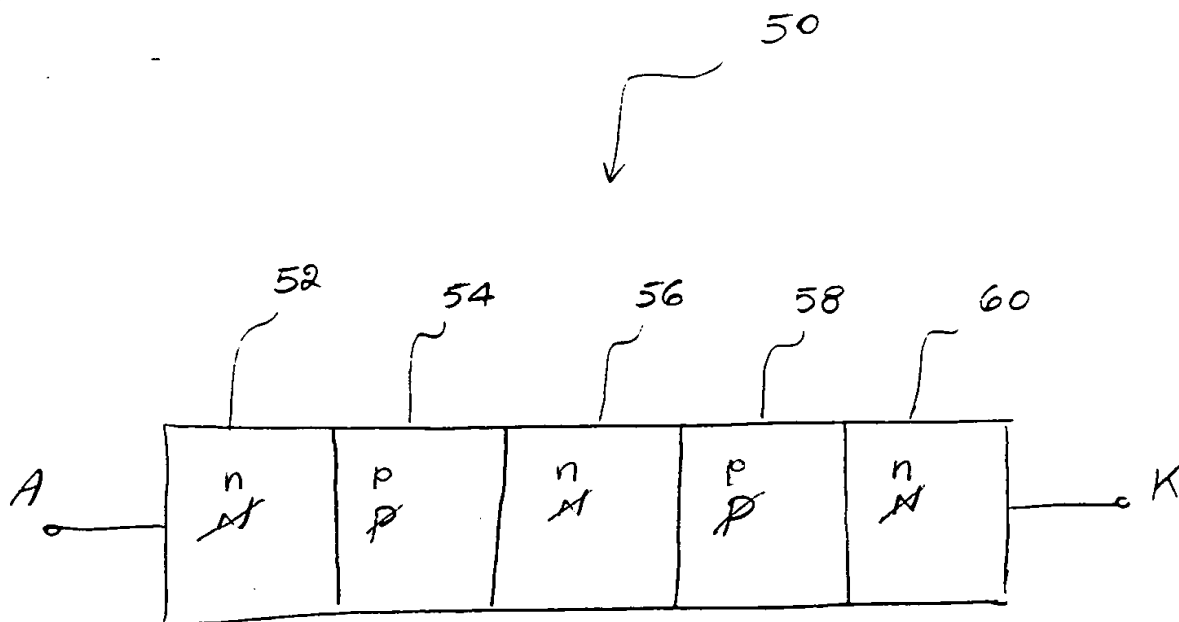


Fig. 2

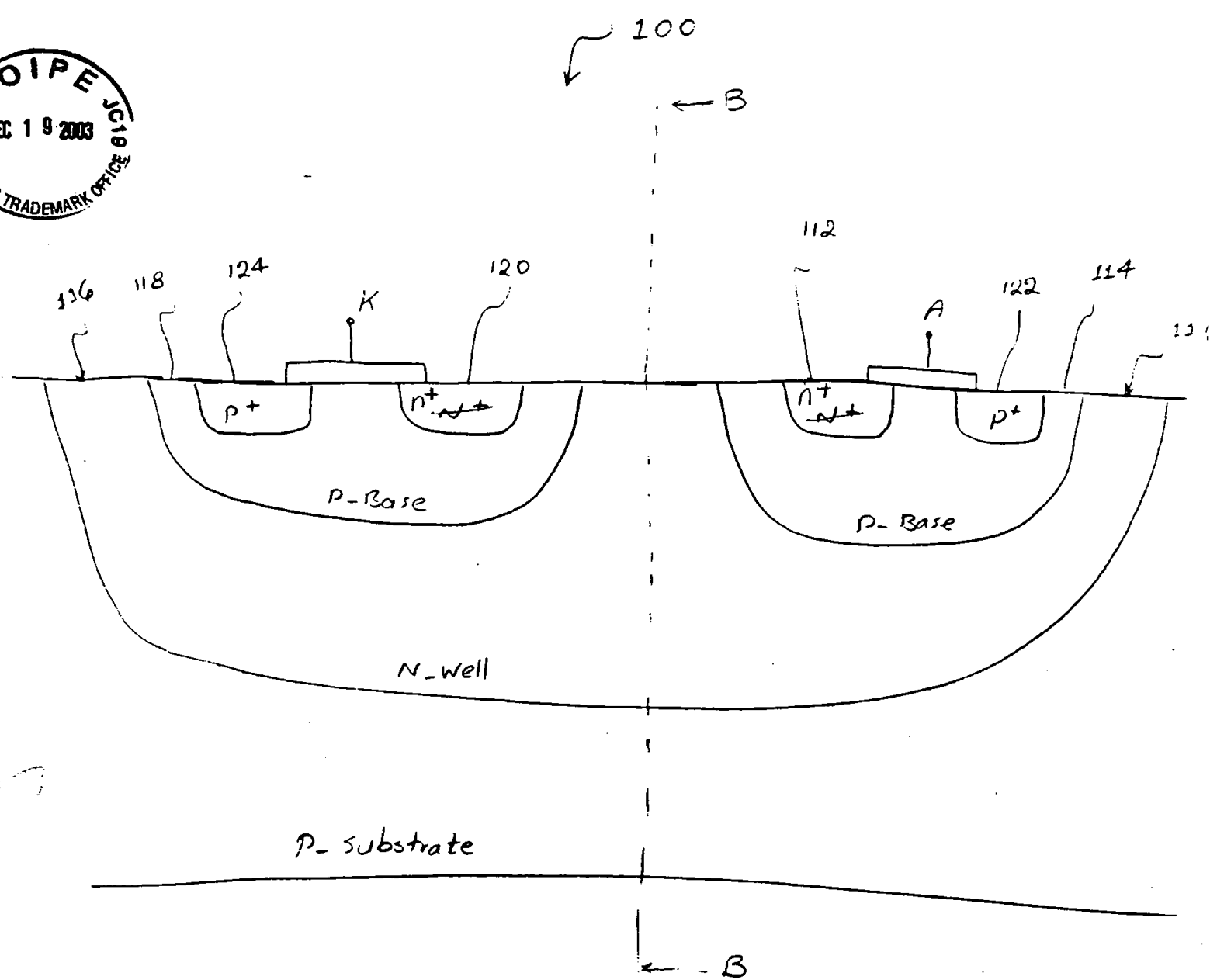


Fig. 3

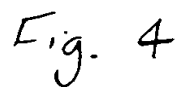
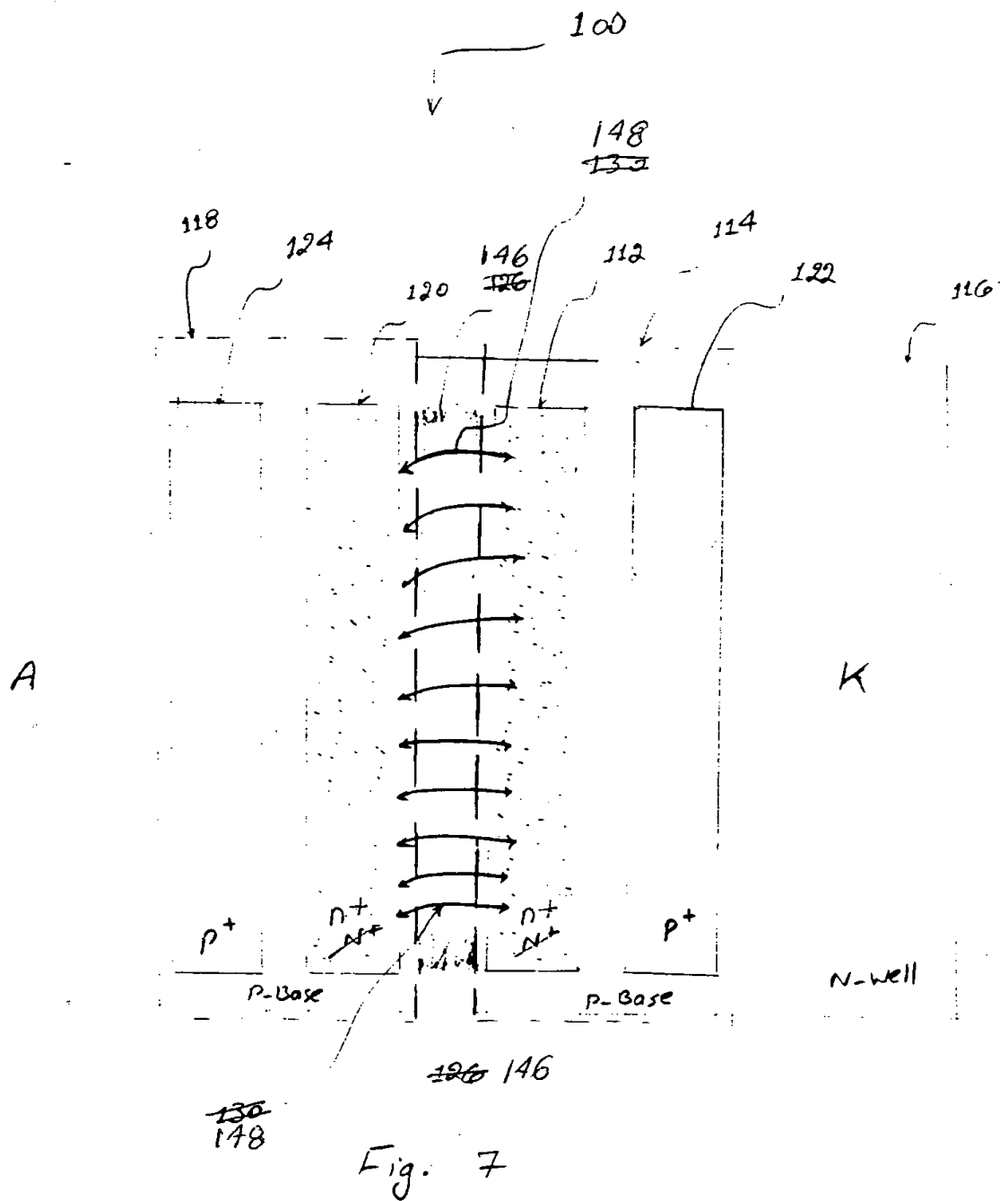
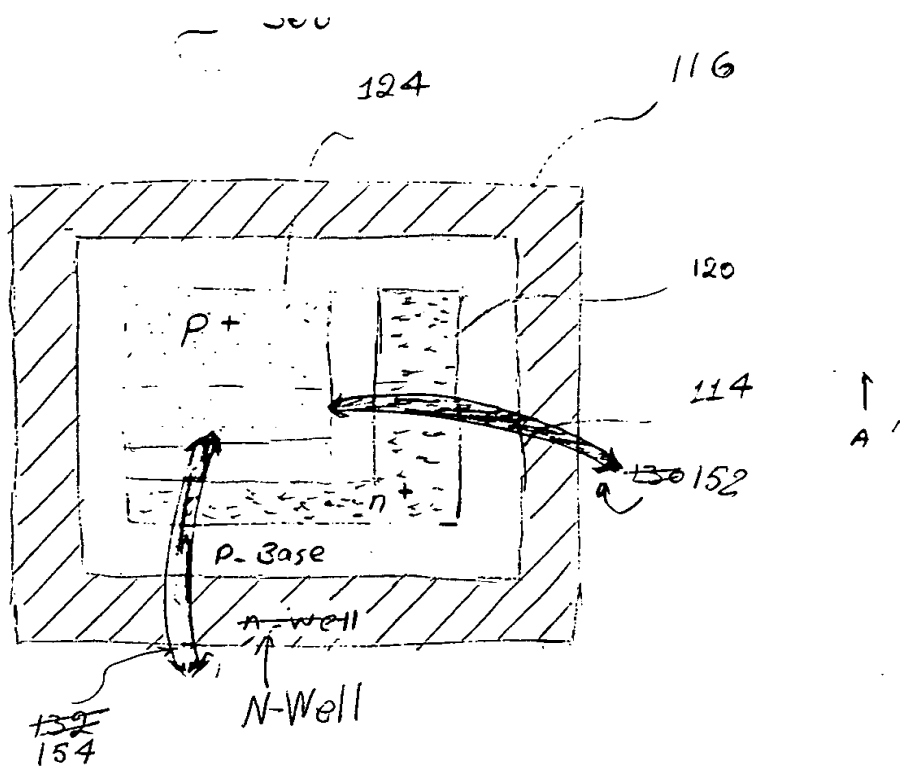






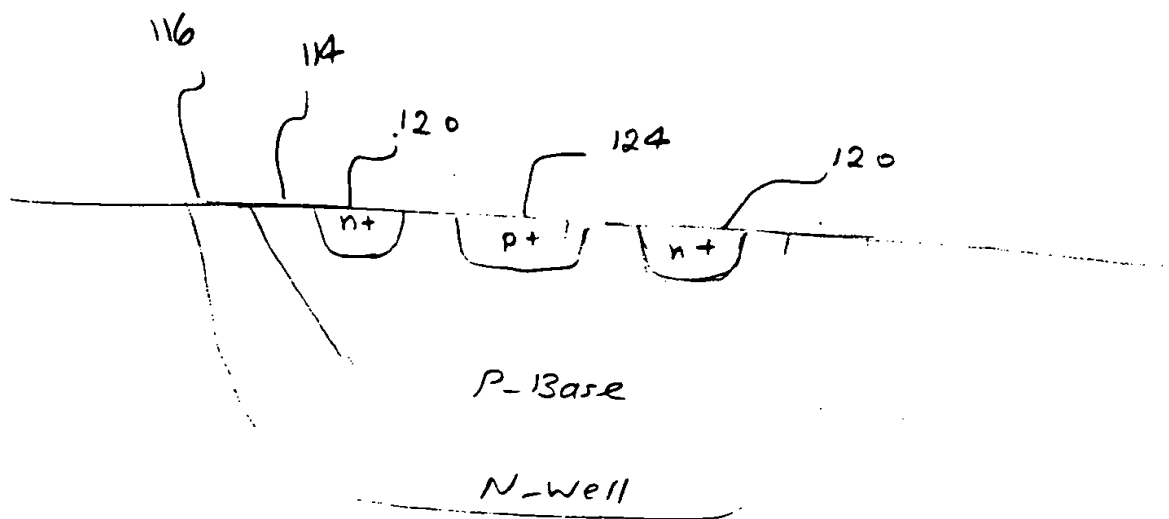
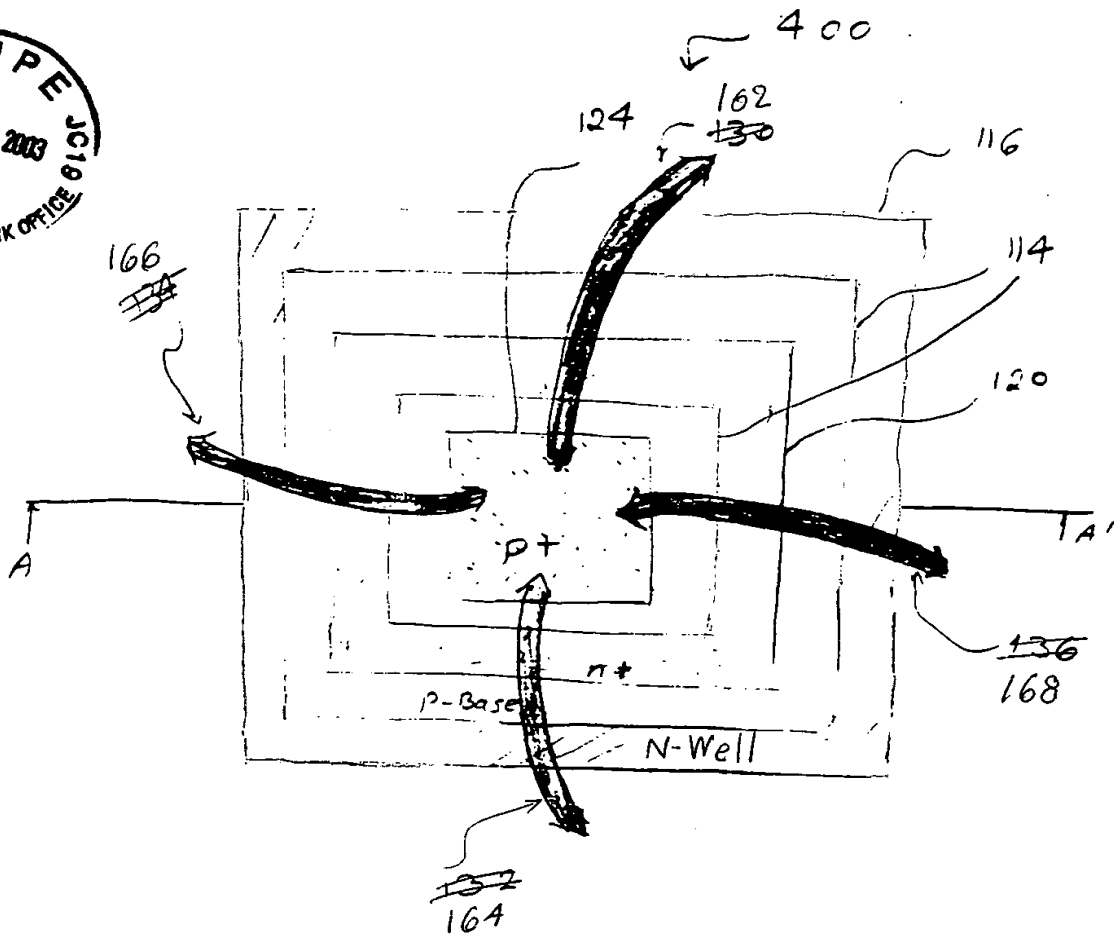
Fig. 6

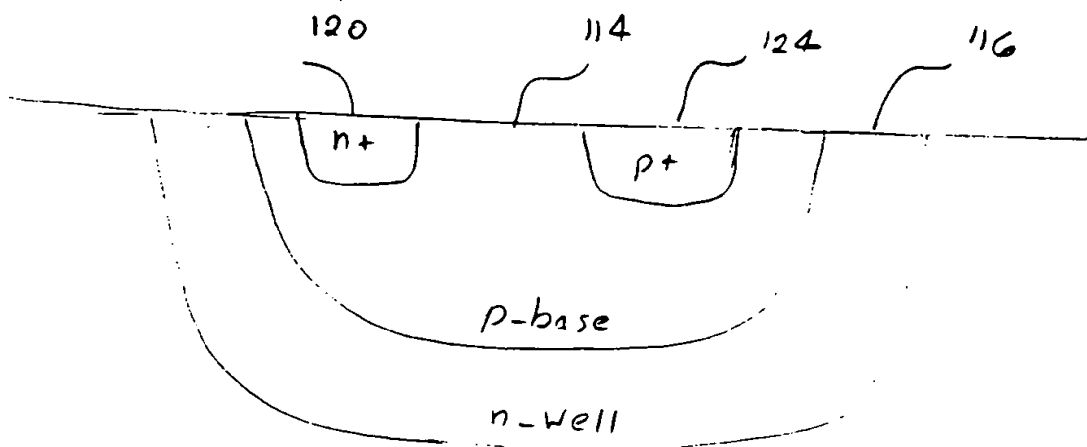
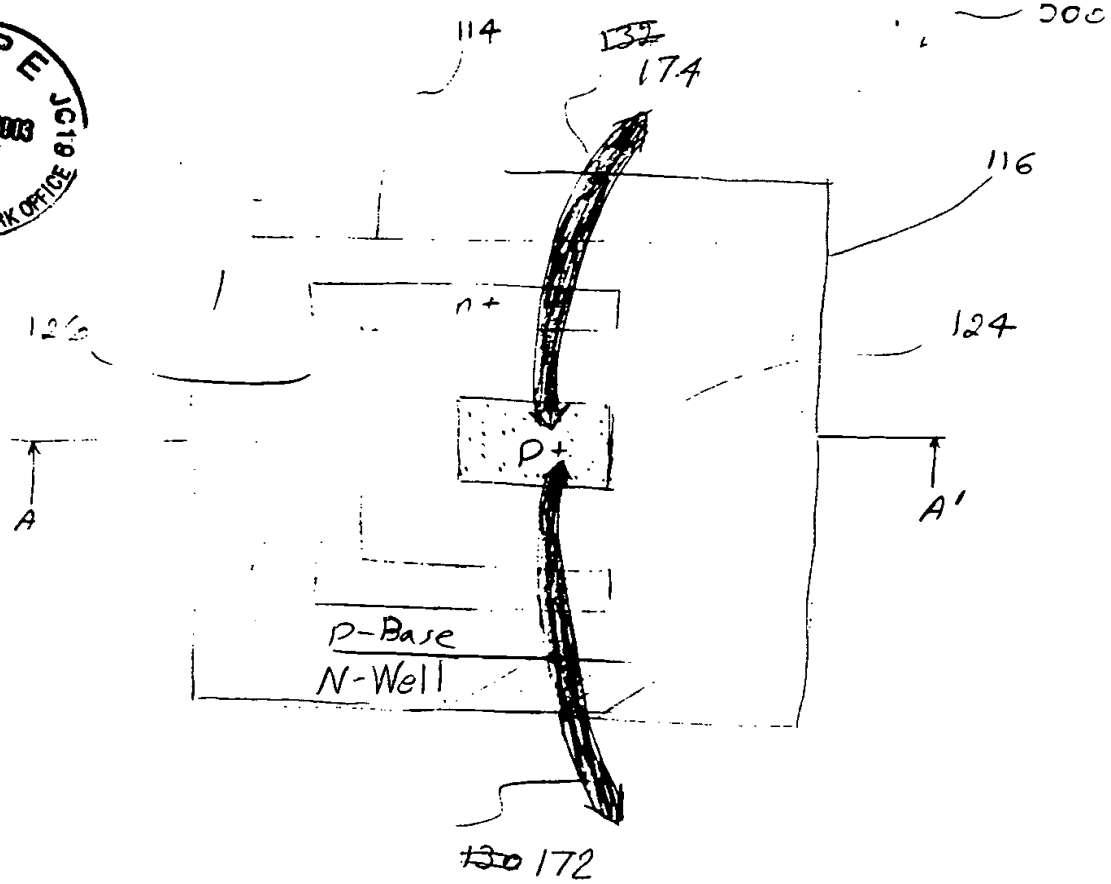




Hand-drawn schematic of a MOSFET cross-section. The diagram shows a central channel region labeled  $p^+$  with a gate stack on top. The gate stack is labeled  $120$  on the right and  $124$  on the left. The channel region is flanked by  $n^+$  regions. The substrate is labeled  $p\text{-Base}$  and  $N\text{-well}$ . The top surface is labeled  $116$  on the left and  $114$  on the right.

Fig. 8B





600

~~178~~  
178

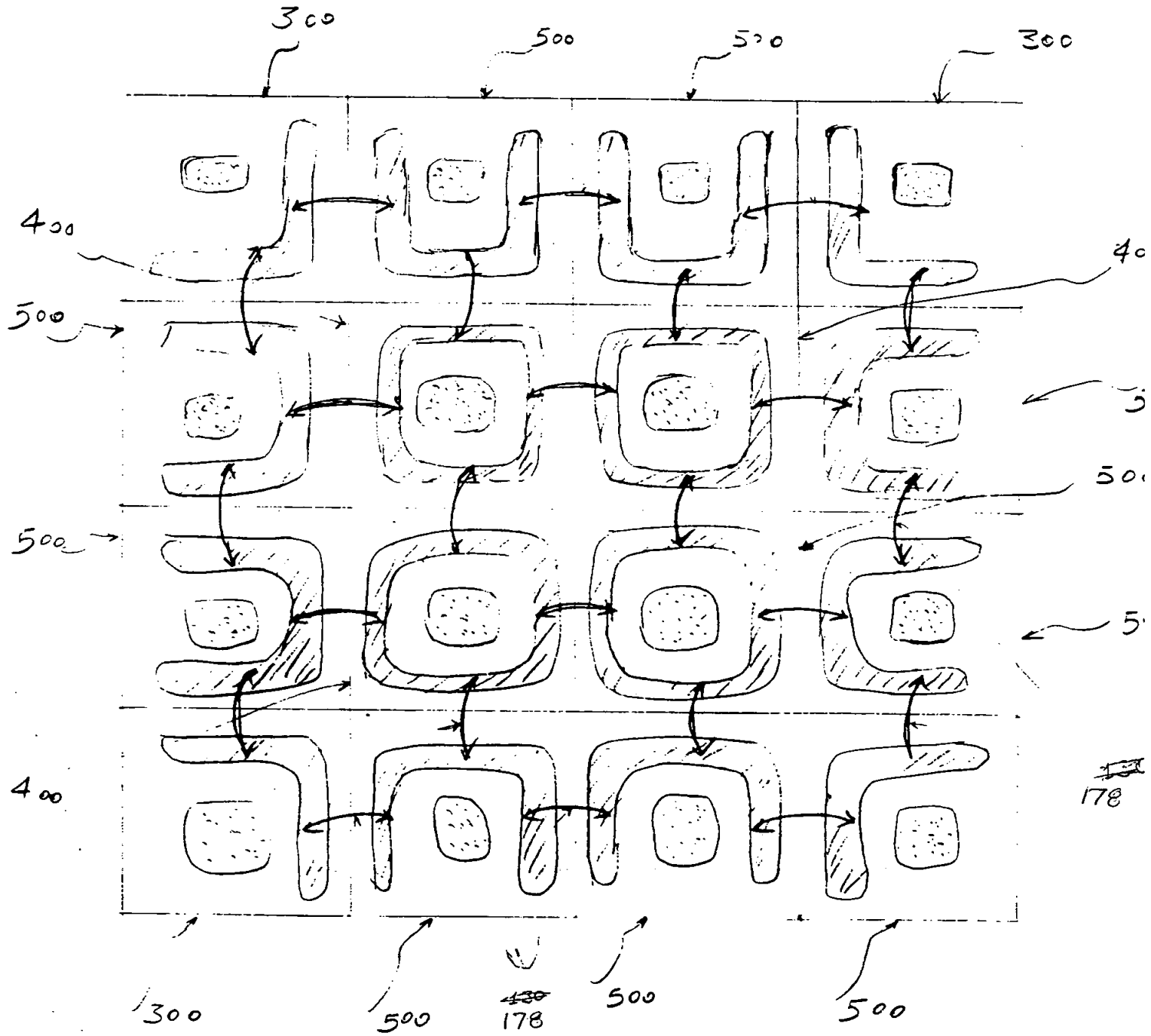


Fig. 11 A

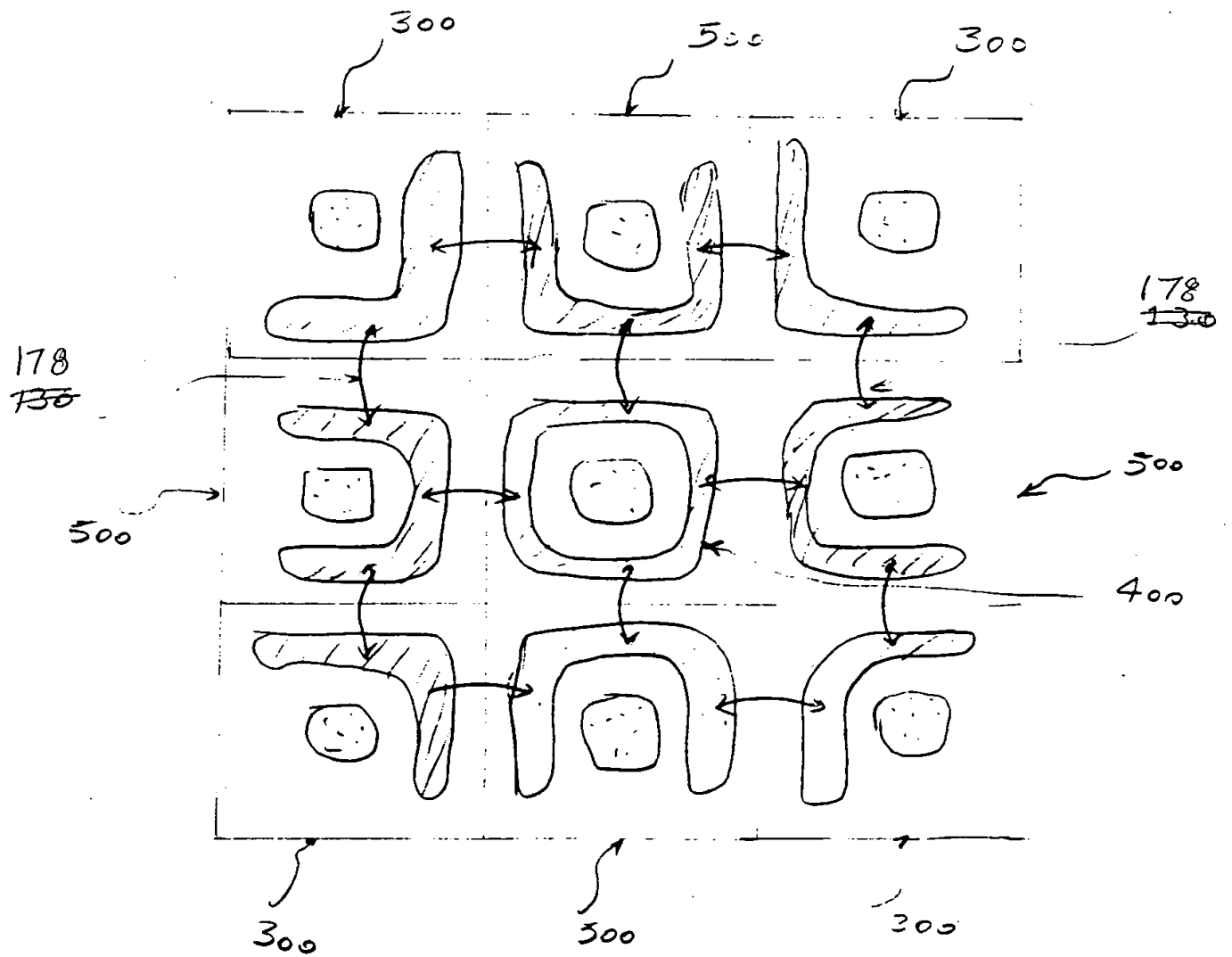


Fig. 11B

700

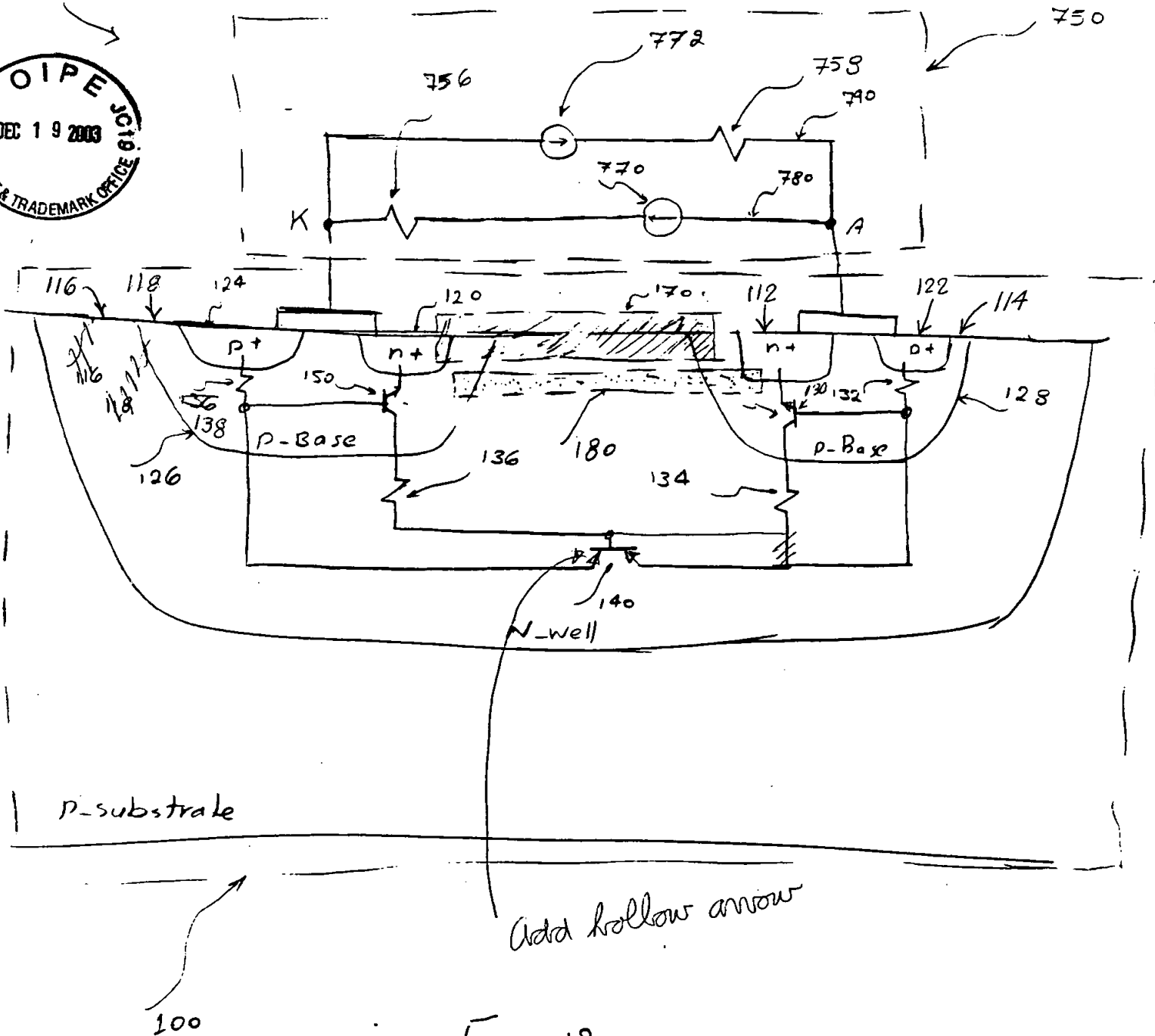


Fig. 12



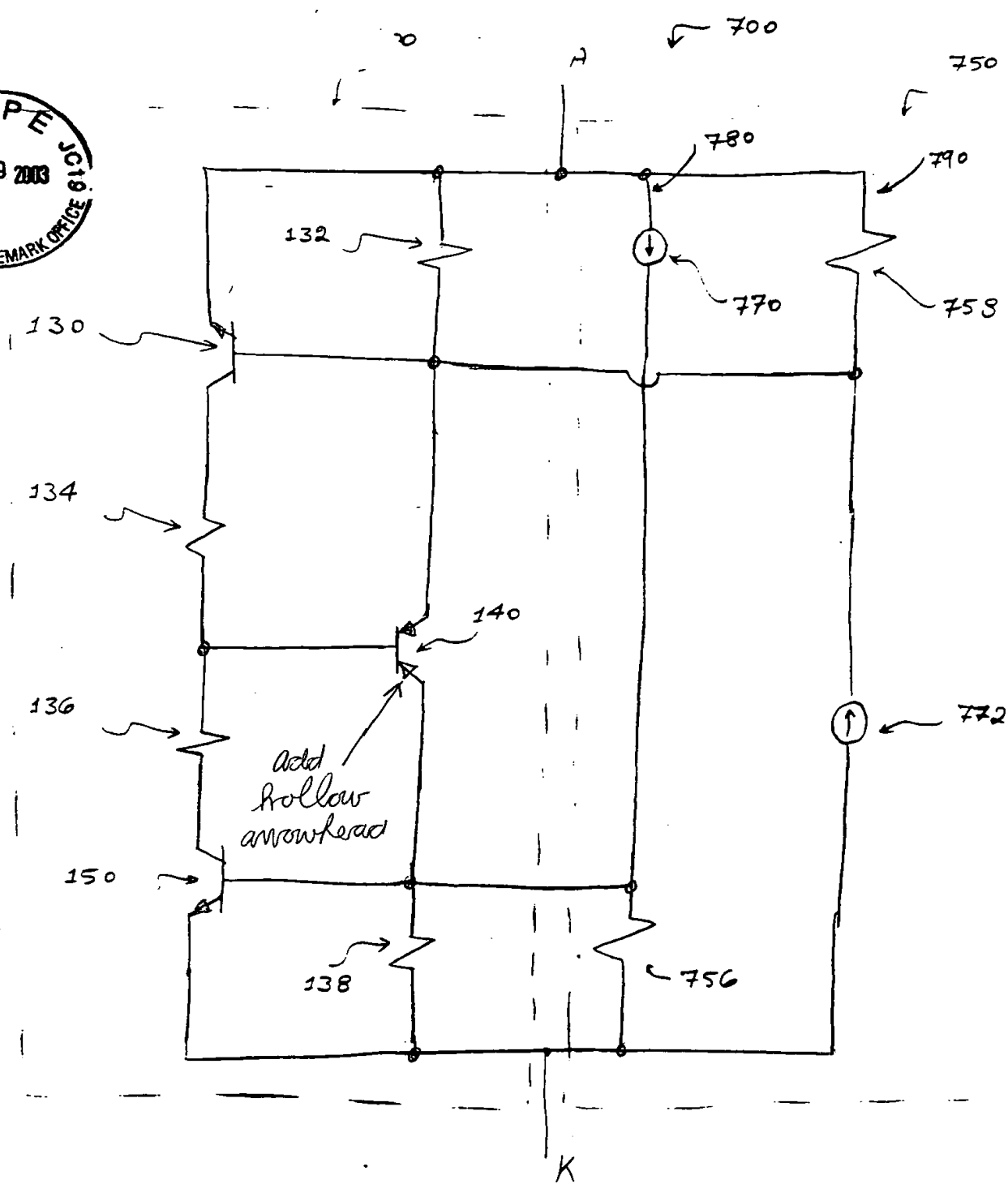


Fig. 13

Fig. 14

